150V Low RDS(ON) MOSFET Increases Efficiency and Output Power in LED Lighting, Solar and Industrial Designs

DC-DC designers need MOSFET solutions that offer lower switching losses and less noise in a compact footprint. Leveraging its advanced process and packaging technologies, as well as system expertise, Fairchild Semiconductor has released a 150V MOSFET with low RDS(ON) (17mOhm MAX) and an optimized Figure of Merit (FOM) (17mOhm * 33nCº Max) to bring high efficiency, lower power dissipation and less heat in a 5mm x 6mm MLP footprint.

The FDMS86200 is designed using shielded-gate MOSFET technology that brings lower switching noise and ringing to the design, contributing to lower EMI. Without this proprietary technology feature, a designer would be forced to choose a 200V MOSFET, which would double the RDS(ON) and lower the overall efficiency. Fairchild’s FDMS86200 also features an improved body diode that boosts switching performance by reducing losses.

Fairchild offers the broadest MOSFET portfolio in the industry, so a designer can choose multiple technologies for the right MOSFET for the application. This unique combination of functional, process and packaging innovation and overall system expertise enables greater innovation for electronic manufacturers. Fairchild’s MOSFET portfolio has a wide range of breakdown voltages (20V-1000V) and advanced packaging technologies ranging from 1mm x 1.5mm WL-CSP to 20mm x 26mm TO264 packaging.

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